

1 4. (amended) The semiconductor light-emitting device according
2 to claim 1, wherein said transparent conductive film is
3 made of In_2O_3 -10 wt.% ZnO.

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1 5. (amended) The semiconductor light-emitting device according
2 to claim 1, wherein said n-type transparent conductive film
3 has a surface with a first surface roughness that is
4 greater than a second surface roughness of a surface of
5 said Au thin film.

Claim 6 is maintained unchanged.

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1 7. (amended) The semiconductor light-emitting device according
2 to claim 4, wherein said transparent conductive film of
3 In_2O_3 -10 wt.% ZnO is formed by laser ablation.

Please cancel claims 8 to 15.

REMARKS:

- 1) We have not yet received a copy of the Notice of Patent Drawing Review (Form PTO-948). Please provide a copy or otherwise indicate if there are any formal defects in the originally filed drawings.
- 2) There is a typographical error in the Examiner's Notice of References Cited (Form PTO-892) enclosed with the Office Action. The